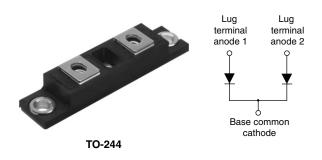
Vishay High Power Products

HEXFRED[®] Ultrafast Soft Recovery Diode, 280 A



SHA

| PRODUCT SUMMARY | | | | |
|--------------------------------------|-----------------|--|--|--|
| I _{F(AV)} | 280 A | | | |
| V _R | 600 V | | | |
| I _{F(DC)} at T _C | 149 A at 100 °C | | | |

FEATURES

- Very low Q_{rr} and t_{rr}
- Lead (Pb)-free
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- · Reduced snubbing

DESCRIPTION

HEXFRED[®] diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|--|-----------------------------------|---|---------------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS | |
| Cathode to anode voltage | V _R | | 600 | V | |
| Continuous forward current | | T _C = 25 °C | 292 | | |
| Continuous forward current | IF | T _C = 100 °C | 149 | А | |
| Single pulse forward current | I _{FSM} | Limited by junction temperature 600 | | | |
| Non-repetitive avalanche energy | E _{AS} | L = 100 μ H, duty cycle limited by maximum T _J | 2.2 | mJ | |
| Maximum power dissipation PD - | | T _C = 25 °C | 657 | W | |
| | | T _C = 100 °C | 263 | vv | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | - 55 to + 150 | °C | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|------------------------|--|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage | V _{BR} | I _R = 100 μA | | 600 | - | - | |
| | | I _F = 105 A | | - | 1.33 | 1.8 | v |
| Maximum forward voltage V _{FM} | I _F = 210 A | See fig. 1 | - | 1.53 | 2.1 | | |
| | | I _F = 105 A, T _J = 125 °C | | - | 1.22 | 1.64 | |
| Maximum reverse leakage current | I _{RM} | $T_{J} = 125 \text{ °C}, V_{R} = 600 \text{ V}$ See fig. 2 | | - | 2.4 | 8 | mA |
| Junction capacitance | CT | V _R = 200 V See fig. 3 | | - | 280 | 400 | pF |
| Series inductance | L _S | From top of terminal hole to mounting plane - 5.0 | | 5.0 | - | nH | |



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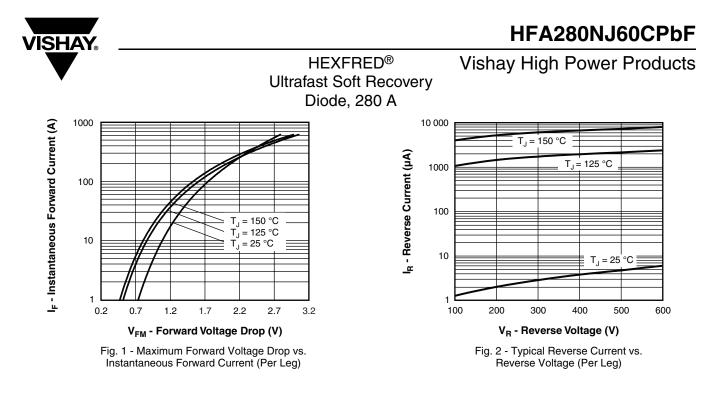
| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified) | | | | | | | | |
|---|-------------------------------|---|--|----------------------------|------|------|-------|-----|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS | |
| Reverse recovery time | | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$ | | - | 39 | - | | |
| See fig. 5 | t _{rr} | T _J = 25 °C | | - | 92 | 140 | ns | |
| | | T _J = 125 °C | - | - | 180 | 270 | | |
| Peak recovery current | | T _J = 25 °C | | - | 9.3 | 17 | ^ | |
| See fig. 6 | I _{RRM} | IRRM | T _J = 125 °C | $I_{\rm F} = 105 {\rm A}$ | - | 16 | 30 | A |
| Reverse recovery charge | Q _{rr} | T _J = 25 °C | dI _F /dt = 200 A/µs V _R = 200 V | - | 490 | 1200 | nC | |
| See fig. 7 | | T _J = 125 °C | | - | 1400 | 4000 | nc | |
| Peak rate of recovery current | Peak rate of recovery current | -11 (-11 | T _J = 25 °C | | - | 290 | - | A./ |
| See fig. 8 | T _J = 125 °C | | - | 200 | - | A/μs | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|--|-------------|-----------------------------------|----------|------|----------|---------------------|--|
| PARAMETER | | SYMBOL | MIN. | TYP. | MAX. | UNITS | |
| Maximum junction and storage temperatur | e range | T _J , T _{Stg} | - 55 | - | 150 | °C | |
| Thermal resistance, junction to case | per leg | D | - | - | 0.19 | 0000 | |
| mermanesistance, junction to case | per module | R _{thJC} | - | - | 0.095 | °C/W K/W | |
| Typical thermal resistance, case to heatsink | | R _{thCS} | - | 0.10 | - | 17, 17 | |
| | | | - | 68 | - | g | |
| Weight | | | - | 2.4 | - | OZ. | |
| Mounting torque | (1) | | 30 (3.4) | - | 40 (4.6) | N | |
| Mounting torque | center hole | | 12 (1.4) | - | 18 (2.1) | N ⋅ m (lbf ⋅ in) | |
| Terminal torque | | | 30 (3.4) | - | 40 (4.6) | | |
| Vertical pull | | | - | - | 80 | lbf ⋅ in | |
| 2" lever pull | | | - | - | 35 | חו י ועו | |

Note

(1) Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film or thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached.





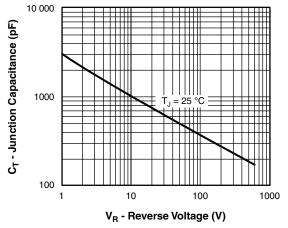


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

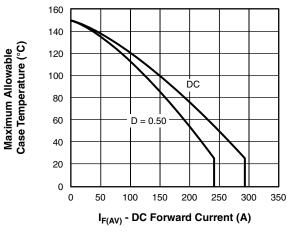


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current (Per Leg)

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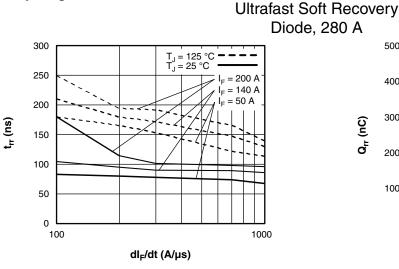


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)

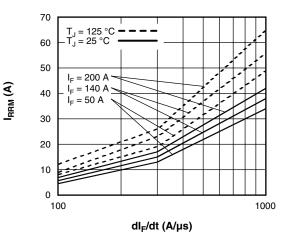
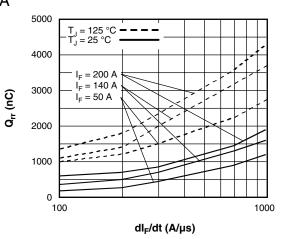


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)



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Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

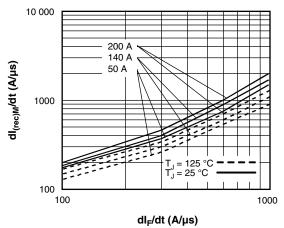
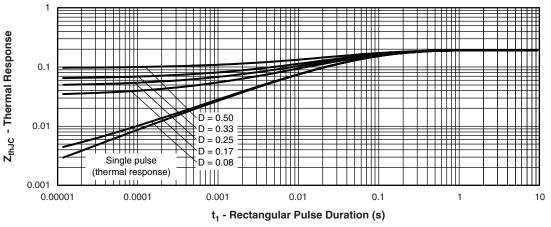


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)



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Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



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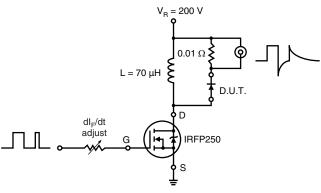
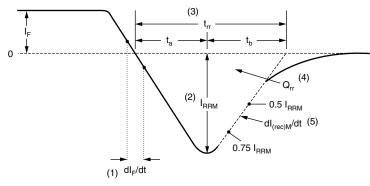


Fig. 10 - Reverse Recovery Parameter Test Circuit



 dl_F/dt - rate of change of current through zero crossing (4) ${\rm Q}_{\rm rr}$ - area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RBM}$

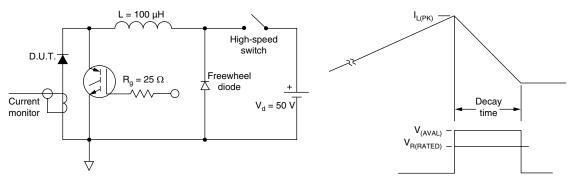
(2) I_{RRM} - peak reverse recovery current

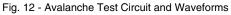
(3) $t_{\rm rr}$ - reverse recovery time measured from zero crossing point of negative going ${\rm I_F}$ to point where a line passing through 0.75 ${\rm I_{RRM}}$ and 0.50 ${\rm I_{RRM}}$ extrapolated to zero current.

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ (5) dI_{(rec)M}/dt - peak rate of change of

current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions



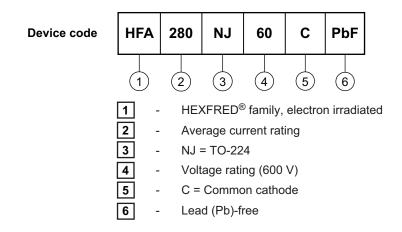


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| Dimensions http://www.vishay.com/doc?95021 | | | | | |
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